HCG100FF170A11

1700V/100A Half Bridge IGBT Module

Description

The HCG100FF170A11 offer lower losses and higher energy for soft switching applications.

Features

- 1700V100 A, VCE (sat)(typ.) = 2.20V
- Lower losses andhigher energy
- Excellent short-circuit capability
- 34 mm half bridge module

Applications

- Motor drive
- Inverter
- Power supply
- Wind Turbines

Circuit diagram

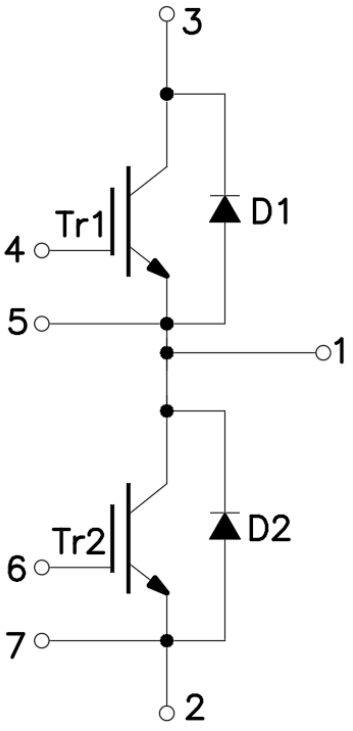

Figure 1. Out drawing & circuit diagram for HCG100FF170A11

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Pin Configuration and Marking Information

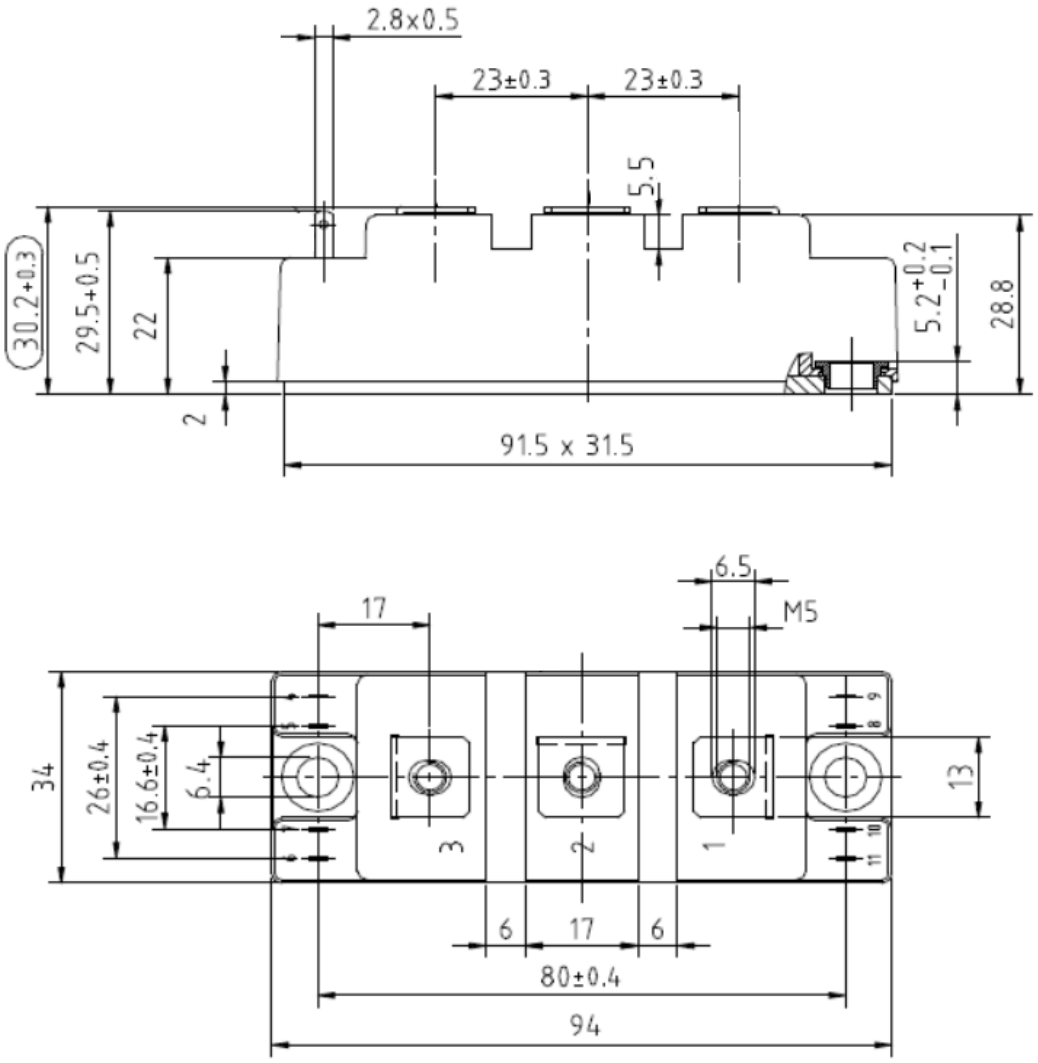

Figure 2. Pin configuration

Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, f = 50Hz, t =1min	2.5	KV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	26 21	mm
Clearance	terminal to heatsink terminal to terminal	23.6 10	mm
CTI	-	>200	-
Module lead resistance, terminals – chip	T_C =25°C	0.8	mΩ
Mounting torque for module mounting	M5, M6	3 to 6	Nm
Weight	-	160	g

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Maximum Ratings (IGBT, T_j =25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	G-E Short	1700	V
V_{GES}	Gate-Emitter Voltage	C-E Short	±30V	V
I_C	DC Continuous Collector Current	T_C =100°C	100	A
I_{CM}	Pulse Collector Current	t_p =1ms, Note1	200	A
P_C	Maximum Power Dissipation	T_C =25°C, T_j =150°C(IGBT)	500	W
T_{jop}	junction temperature	-	-40 to 150	°C
T_{stg}	Storage temperature	-	-40 to 125	°C

Note1: Pulse width limited by maximum junction temperature

Maximum Ratings (Freewheeling diode, T_j =25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{RRM}	Peak Repetitive Revers Voltage	-	1700	V
I_F	Diode forward Current	- Tc =100°C	100	A
I_{FRM}	Repetitive peak forward Current	t_p =1ms, Note1	200	A
T_{jop}	junction temperature	-	-40 to 150	°C
T_{stg}	Storage temperature	-	-40 to 125	°C

Note1: Pulse width limited by maximum junction temperature

IGBT Electrical characteristics (T_j =25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C =100A, V_{GE} =15V	T_j =25°C	-	2.20	2.50	V
			T_j =125°C	-	2.60	-	V
$V_{GE(th)}$	Gate-Emitter threshold Voltage	I_C =1mA, V_{CE} =V_{GE}		4.5	-	5.7	V
Q_G	Gate charge	V_{GE} = -15V to +15V		-	1000	-	nC
R_{Gint}	Internal gate resistor	f=1M, Vpp=1V	T_j =25°C	-	5.25	-	Ω
C_{ies}	Input Capacitance	V_{CE} =25V, V_{GE} =0V, f =1MHz	T_j =25°C	-	8.6	-	nF
C_{oes}	Output Capacitance			-	1.29	-	nF
C_{res}	Reverse transfer Capacitance			-	0.8	-	nF
I_{CES}	Collector- Emitter Cut off Current	V_{CE} =1700V, V_{GE} =0V	T_j =25°C	-	-	5	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE} = ±30V, V_{CE} =0V	T_j =25°C	-	-	400	nA
$t_{d(on)}$	Turn-on delay time	V_{CC} = 900V, I_C = 100A, R_G = 5.1Ω, V_{GE} = ±15V, Inductive Load	T_j =25°C	-	180	-	ns
			T_j =125°C	-	200	-	
t_r	Rise time		T_j =25°C	-	55	-	ns
			T_j =125°C	-	50	-	
$t_{d(off)}$	Turn-off delay time		T_j =25°C	-	360	-	ns
			T_j =125°C	-	400	-	

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t_f	Fall time	V_{CC} = 900V I_C = 100A R_G = 5.1Ω V_{GE} = ±15V Inductive Load	T_j=25°C	-	440	-	ns
			T_j=125°C	-	660	-	
E_{on}	Turn-on power dissipation		T_j=25°C	-	15	-	mJ
			T_j=125°C	-	20	-	
E_{off}	Turn-off power dissipation		T_j=25°C	-	20	-	mJ
			T_j=125°C	-	28	-	
$R_{th(j-c)}$	Thermal Resistance, Junction to Case (IGBT)			-		0.25	°C/W

Freewheeling Diode Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V_F	Diode Forward Voltage	I_F =100A, V_{GE} =0V	T_j=25°C	-	3.1	3.3	V
			T_j=125°C	-	3.2	-	
t_{rr}	Diode Reverse Recovery Time	I_F=100A, di/dt= 2100A/μs, V_R=900V, V_{GE} = -15V	T_j=25°C		90		nS
			T_j=125°C		250		
I_{rr}	Peak reverse recovery Current		T_j=25°C	-	75	-	A
			T_j=125°C	-	85	-	
Q_{rr}	Recovered charge		T_j=25°C	-	4	-	uC
			T_j=125°C	-	9	-	
E_{rr}	Reverse recovered energy		T_j=25°C	-	2.4	-	mJ
			T_j=125°C	-	4.7	-	
$R_{th(j-c)}$	Thermal Resistance, Junction to Case (Diode)			-		0.3	°C/W

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Test Conditions

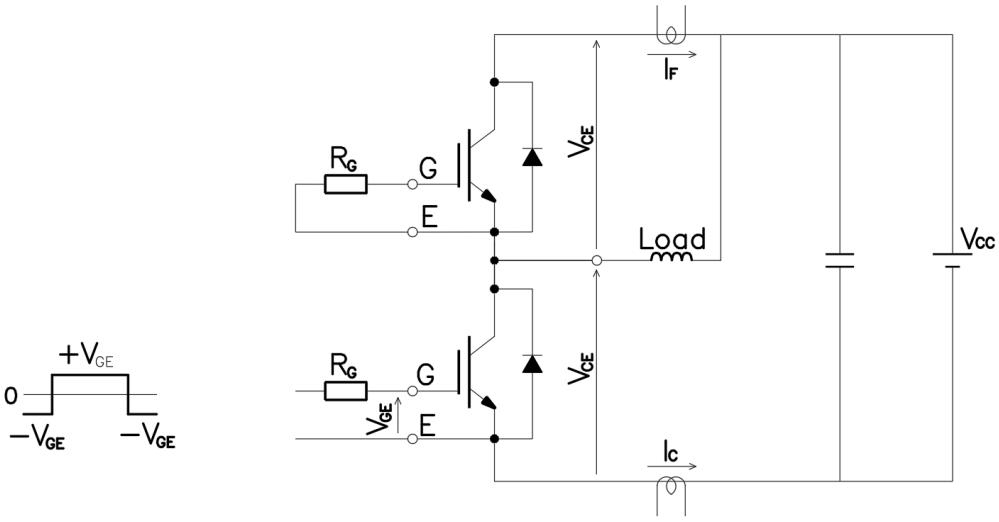

Figure 3. Switching time measure circuit

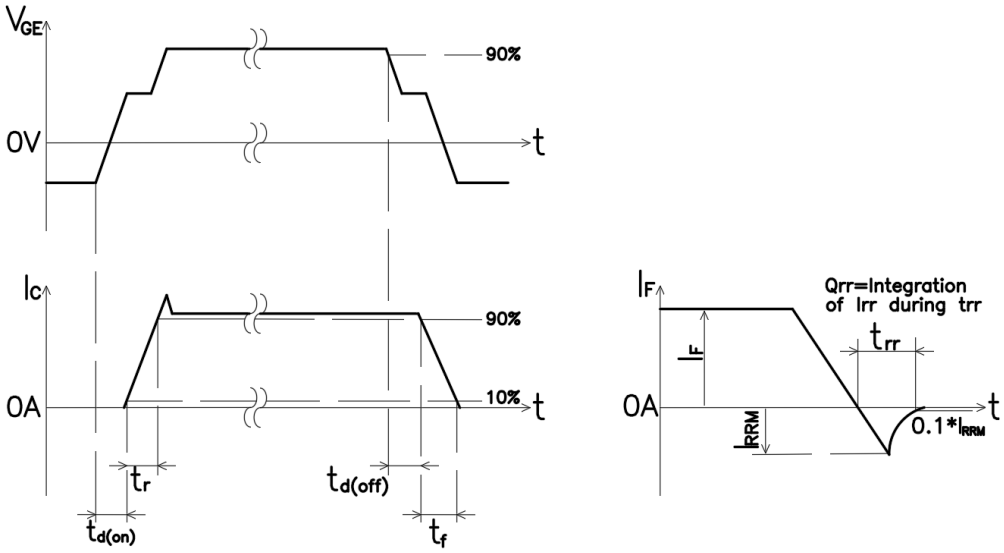

Figure 4. Switching time definition

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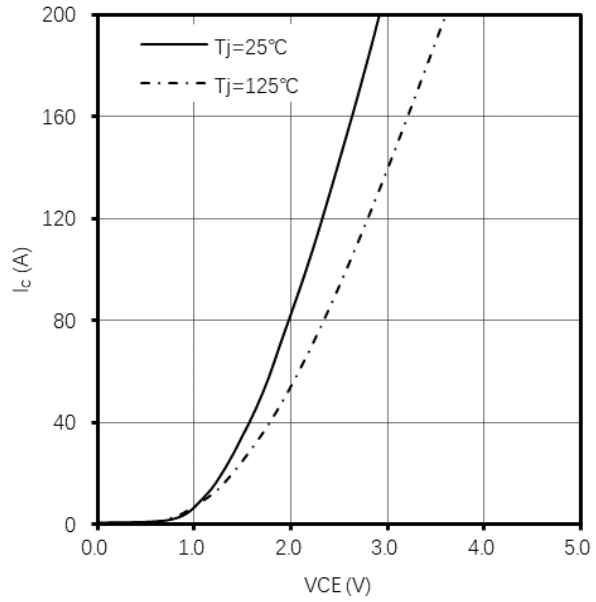

Figure 5. Ic vs V_{CE}
V_{GE} =15V

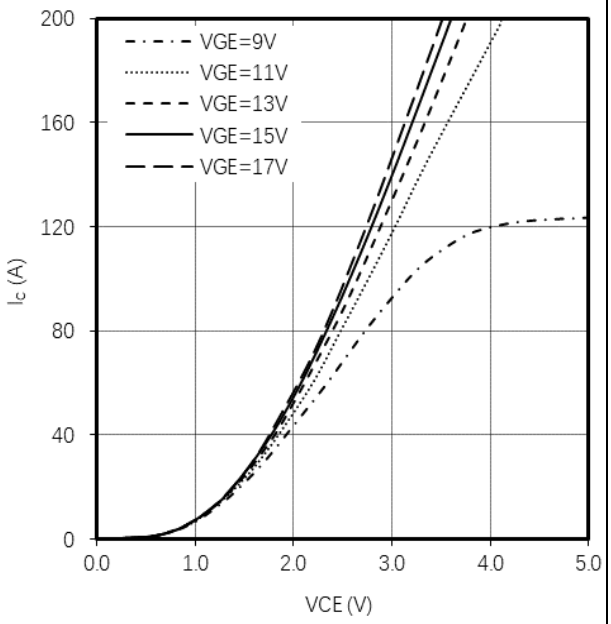

Figure 6. Ic vs V_{CE}
T_j =125°C

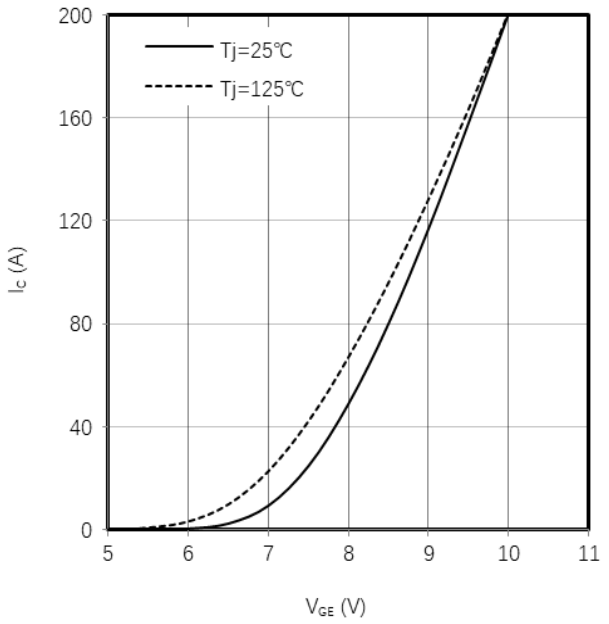

Figure 7. Ic vs V_{GE}
V_{CE} =20V

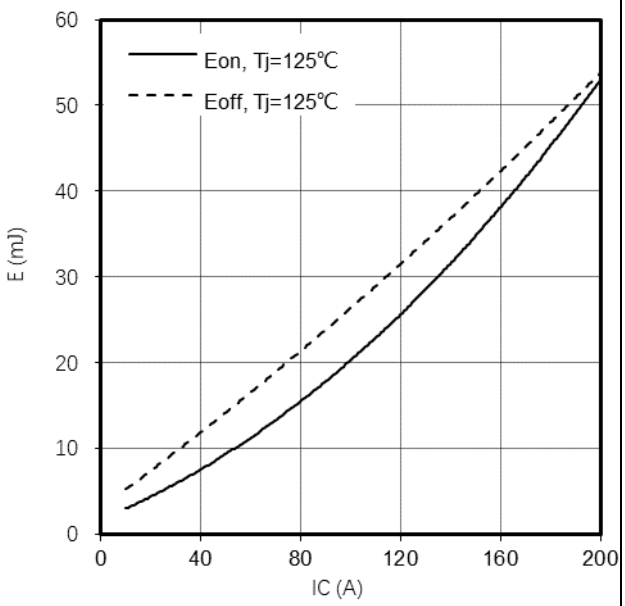

Figure8. E_{on}, E_{off} vs Ic(Typ)
V_{CC}=900V, V_{GE} =+15V/-15V, R_G =5.1Ω

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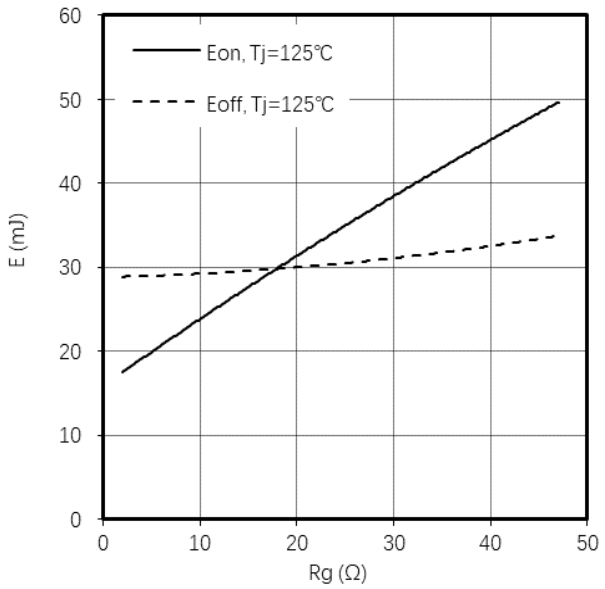

Figure 9. E_{on}, E_{off} vs R_g(Typ)
V_{CC} =900V, V_{GE} =+15V/-15V, I_C =100A

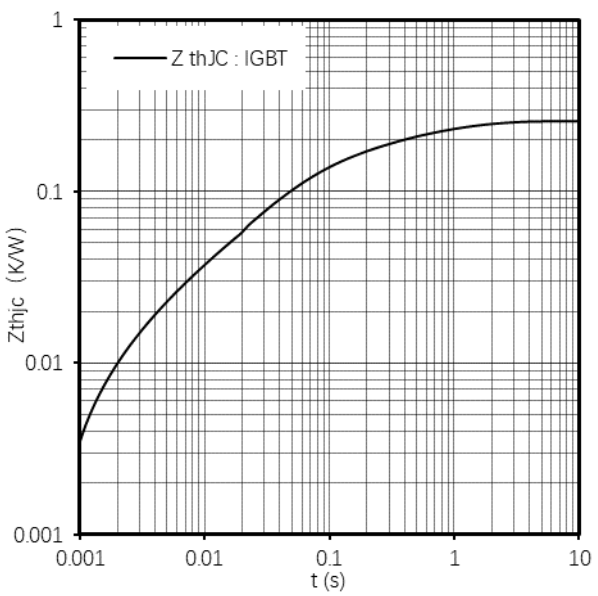

Figure 10. Transient thermal impedance IGBT , Zthjc=f(t)

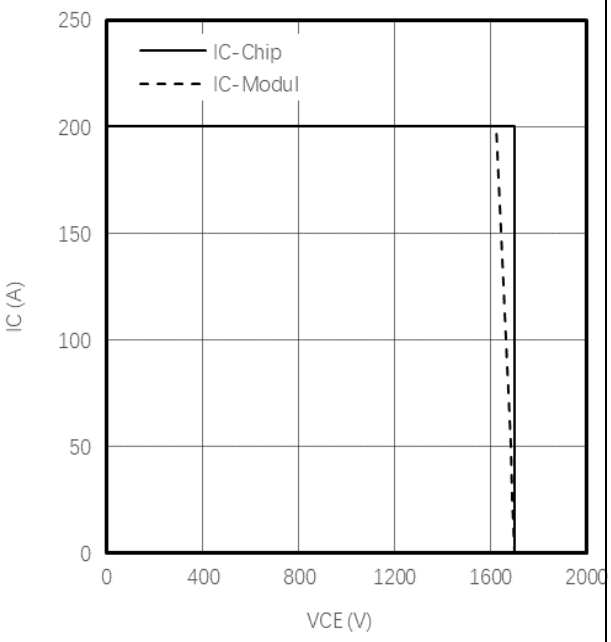

Figure 11. Reverse bias safe operating area IGBT, I_C=f(V_{CE}),V_{GE}=±15V,R_{Goff}=5.1Ω， Tvj=125℃

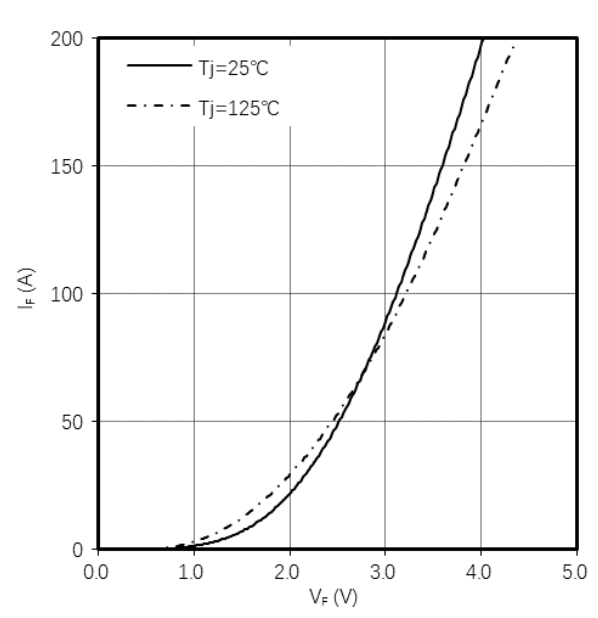

Figure 12. Forward characteristic of Diode ， I_F=f(V_F)

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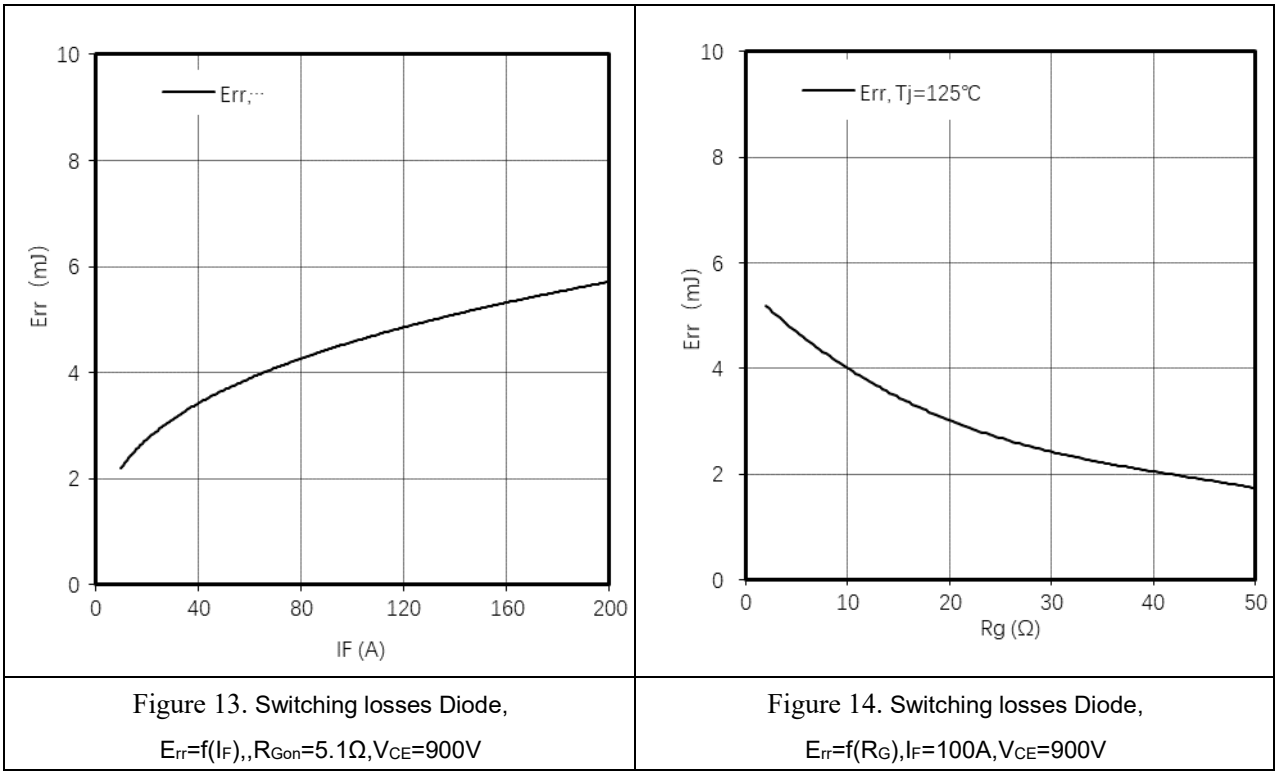

Figure 13. Switching losses Diode, $E_{rr}=f(I_F)$,,$R_{Gon}=5.1\Omega$,$V_{CE}=900V$

Figure 14. Switching losses Diode, $E_{rr}=f(R_G)$,$I_F=100A$,$V_{CE}=900V$

IMPORTANT NOTICE:

This product data sheet describes the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively under the terms and conditions of the supply agreement. There will be no guarantee or of any kind for the product and its characteristics.

The data contained in this document is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the product's suitability for the intended application and the completeness of the product data concerning such application.

Due to technical requirements, our product may contain dangerous substances. For information on the types in question, please contact the sales staff responsible for you.

Changes to this product data sheet are reserved.

Please contact the sales staff (Email:sales@hiitio.com) for further information on the product, technology, delivery terms, conditions and prices.

Instruction note

Naming rules for power module product models（Industrial module）

Product Model							
	HC	G	100	FF	120	E3	A

Hecheng Code

Module type G : IGBT module
D : FRD module
S : SiC module
H : Si/SiC hybrid

Current level (A) 50~900

Topology structure FZ : A switch unit FF : Half bridge
FS : Three phase F4 : H Bridge
F3L : Three level DF : Boost Circuit
FD : Braking Circuit
FP : Rectification+Inverter+Control move
AL : ANPC CL : Chopper

Voltage level (x10)（V） 650~2200

Packaging form+features（A…Z）

A1： 34 mm	A2： 62 mm	
B1： Easy 1B	B1A	B1B…
B2： Easy 2B…	B3： Easy 3B…	
D1： Flow0	D2： Flow1	D3： Flow2
E0 : E0	E1： Econo 2…	E2： E2
E3： ED3	E4 : E4	E5 : ED3S
E6 : EPM2	E7 : EPM3	E8 : EconoPIM3
E9 : ED3H	F0 : F0	P2 : EPM2

Feature :A: Special Code Nil: Standard

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